

isc Silicon PNP Power Transistor

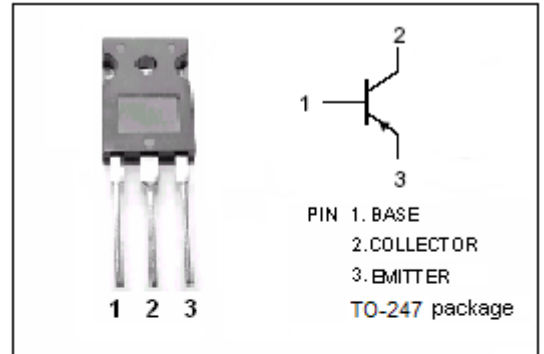
MJW21191

DESCRIPTION

- DC Current Gain
- High Area of Safe Operation

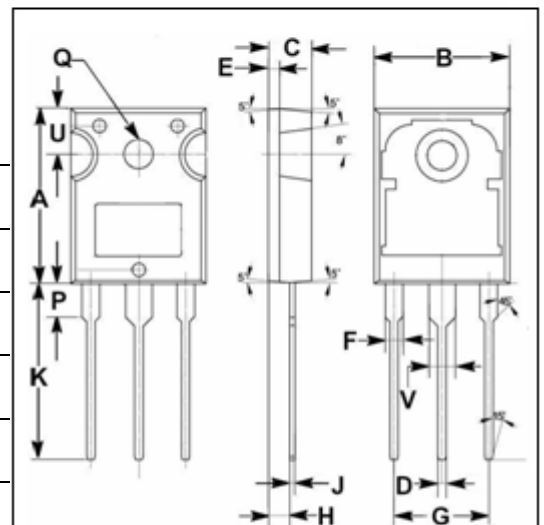
APPLICATIONS

- Designed for power audio output, or high power drivers in audio amplifiers.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Emitter Voltage	-150	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-8	A
I _{CM}	Collector Current-Pulsed	-16	A
I _B	Base Current-Continuous	-2	A
P _D	Total Power Dissipation (T _C =25°C)	100	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65~150	°C



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-C}	ThermalResistance Junction To Case	0.65	°C/W

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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =-10mA; I _B =0	-150			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C =-4A ; I _B =-0.4A			-1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C =-8A ; I _B =-1.6A			-2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C =-4A ; V _{CE} =-2V			-2	V
I _{CEs}	Collector Cutoff Current	V _{CE} = -250V; I _E =0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} =-5V; I _C =0			-10	μ A
h _{FE-1}	DC Current Gain	I _C =-4A; V _{CE} =-2V	15		100	
h _{FE-2}	DC Current Gain	I _C =-8A; V _{CE} =-2V	5			
f _T	Current Gain-Bandwidth Product	I _C =-1A ; V _{CE} =-10V; f _{test} =1MHz	4			MHz